

# FDP8030L/FDB8030L

## N-Channel Logic Level PowerTrench® MOSFET

### General Description

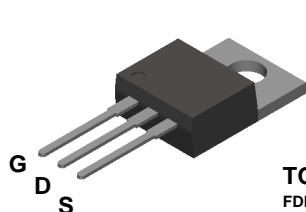
This N-Channel Logic level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable  $R_{DS(on)}$  specifications.

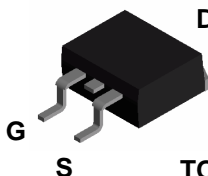
The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

### Features

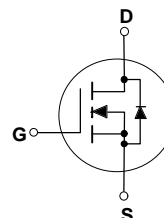
- 80 A, 30 V.  $R_{DS(on)} = 0.0035 \Omega @ V_{GS} = 10 \text{ V}$   
 $R_{DS(on)} = 0.0045 \Omega @ V_{GS} = 4.5 \text{ V}$
- Critical DC electrical parameters specified at elevated temperature
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor
- High performance trench technology for extremely low  $R_{DS(on)}$
- 175°C maximum junction temperature rating



**TO-220**  
FDP Series



**TO-263AB**  
FDB Series



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous (Note 1)	80	A
	– Pulsed (Note 1)	300	
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	187	W
		1.25	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-65 to +175	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	275	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ\text{C/W}$

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

**Drain-Source Avalanche Ratings (Note 1)**

$W_{DSS}$	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 20\text{ V}, I_D = 80\text{ A}$			1500	mJ
$I_{AR}$	Maximum Drain-Source Avalanche Current				80	A

**Off Characteristics**

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		23		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate-Body Leakage, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

**On Characteristics (Note 2)**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1	1.5	2	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-5		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 80\text{ A}$ $T_J = 125^\circ\text{C}$		3.1 4.0	3.5 5.6	m $\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 70\text{ A}$		3.6	4.5	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 10\text{ V}$	60			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 80\text{ A}$		170		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}$		10500		pF
$C_{oss}$	Output Capacitance	$f = 1.0\text{ MHz}$		2700		pF
$C_{riss}$	Reverse Transfer Capacitance			1650		pF

**Switching Characteristics (Note 2)**

$t_{D(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}, I_D = 50\text{ A}$		20	35	ns
$t_r$	Turn-On Rise Time	$V_{GS} = 4.5\text{ V}, R_{GEN} = 10\ \Omega$		185	225	ns
$t_{D(off)}$	Turn-Off Delay Time	$R_{GS} = 10\ \Omega$		160	200	ns
$t_f$	Turn-Off Fall Time			200	240	ns
$Q_g$	Total Gate Charge	$V_{DS} = 15\text{ V}$		120	170	nC
$Q_{gs}$	Gate-Source Charge	$I_D = 80\text{ A}, V_{GS} = 5\text{ V}$		27		nC
$Q_{gd}$	Gate-Drain Charge			48		nC

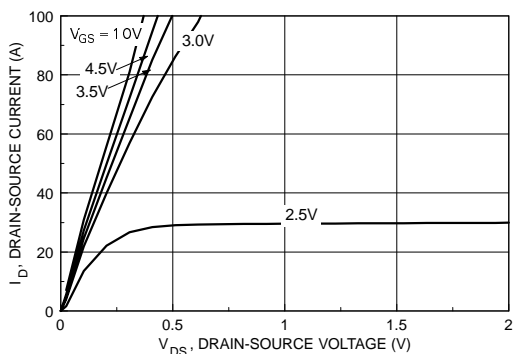
**Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current (Note 1)				80	A
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current (Note 1)				300	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 80\text{ A}$ (Note 1)		1	1.3	V

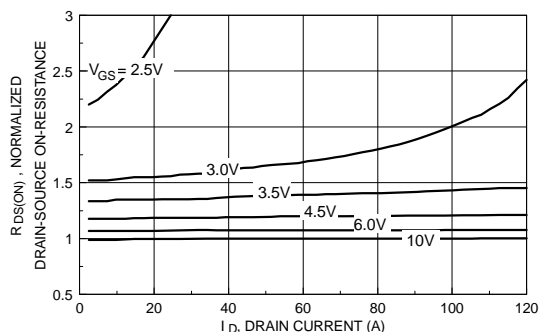
**Notes:**

1. Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty Cycle < 2.0%

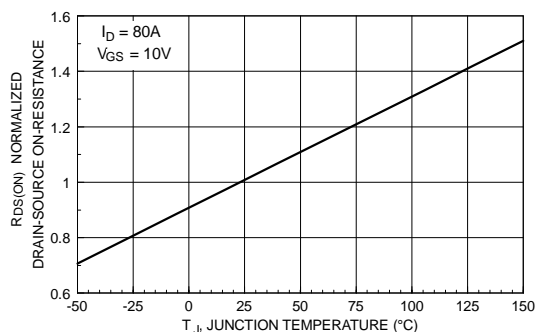
## Typical Characteristics



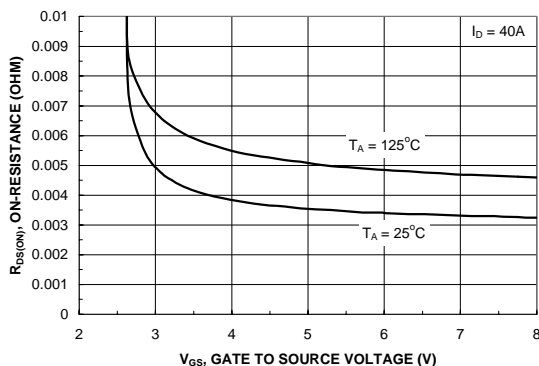
**Figure 1. On-Region Characteristics.**



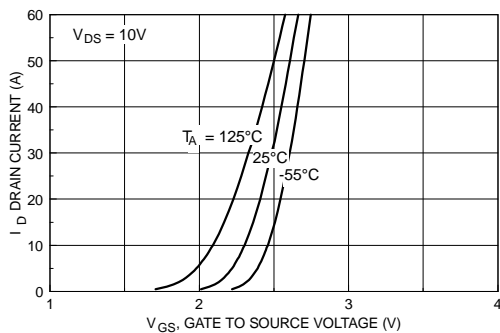
**Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.**



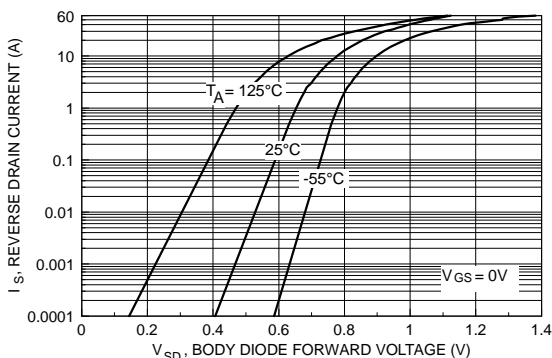
**Figure 3. On-Resistance Variation with Temperature.**



**Figure 4. On-Resistance Variation with Gate-to-Source Voltage.**



**Figure 5. Transfer Characteristics.**



**Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.**

## Typical Characteristics

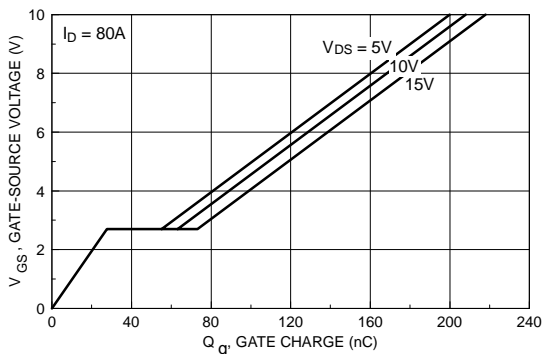


Figure 7. Gate Charge Characteristics.

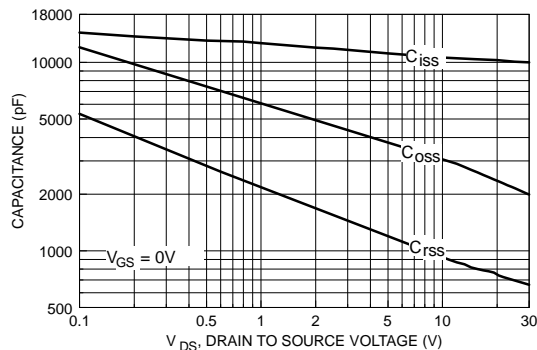


Figure 8. Capacitance Characteristics.

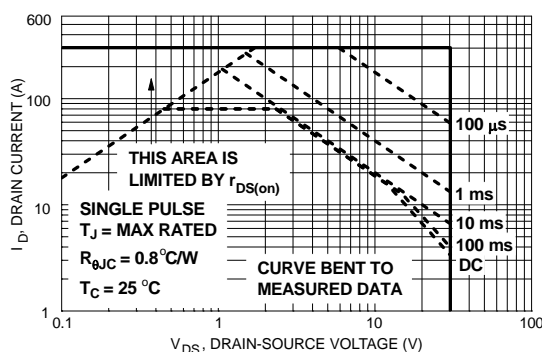


Figure 9. Maximum Safe Operating Area.

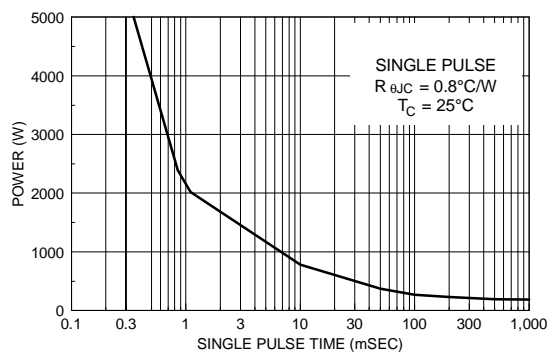


Figure 10. Single Pulse Maximum Power Dissipation.

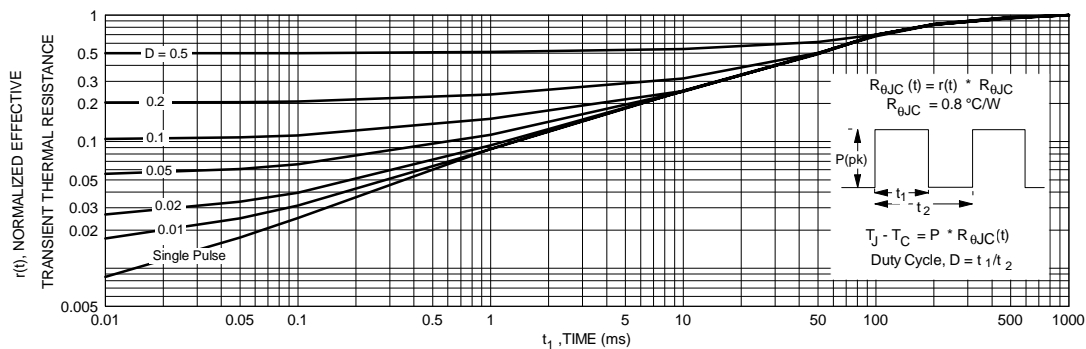


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.



**TRADEMARKS**

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

- |                          |   |                  |
|--------------------------|---|------------------|
| 2Cool™                   | FPS™  | Sync-Lock™       |
| AccuPower™               | F-PFST™   | SYSTEM GENERAL®  |
| AX-CAP®*                 | FRFET®  | TinyBoost™       |
| BitSiC™                  | Global Power Resource <sup>SM</sup>             | TinyBuck™        |
| Build it Now™            | Green Bridge™                                   | TinyCalc™        |
| CorePLUS™                | Green FPS™                                      | TinyLogic®       |
| CorePOWER™               | Green FPS™ e-Series™                            | TINYOPTO™        |
| CROSSVOLT™               | Gmax™   | TinyPower™       |
| CTL™                     | GTO™  | TinyPWM™         |
| Current Transfer Logic™  | IntelliMAX™                                     | TinyWire™        |
| DEUXPEED®                | ISOPLANAR™                                      | TranSiC®         |
| Dual Cool™               | Marking Small Speakers Sound Louder and Better™ | TriFault Detect™ |
| EcoSPARK®                | MegaBuck™                                       | TRUECURRENT®*    |
| EfficientMax™            | MICROCOUPLER™                                   | µSerDes™         |
| ESBC™                    | MicroFET™                                       | SerDes®          |
| Fairchild®               | MicroPak™                                       | UHC®             |
| Fairchild Semiconductor® | MicroPak2™                                      | Ultra FRFET™     |
| FACT Quiet Series™       | MillerDrive™                                    | UniFET™          |
| FACT®                    | MotionMax™                                      | VCX™             |
| FAST®                    | mWSaver™  | VisualMax™       |
| FastvCore™               | OptoHit™  | VoltagePlus™     |
| FETBench™                | OPTOLOGIC®                                      | XS™              |
|                          | OPTOPLANAR®                                     |                  |
|                          | PowerTrench®                                    |                  |
|                          | PowerXS™  |                  |
|                          | Programmable Active Droop™                      |                  |
|                          | QFET®   |                  |
|                          | QS™   |                  |
|                          | Quiet Series™                                   |                  |
|                          | RapidConfigure™                                 |                  |
|                          | Saving our world, 1mW/W/kW at a time™           |                  |
|                          | SignalWise™                                     |                  |
|                          | SmartMax™                                       |                  |
|                          | SMART START™                                    |                  |
|                          | Solutions for Your Success™                     |                  |
|                          | SPM®  |                  |
|                          | STEALTH™  |                  |
|                          | SuperFET®                                       |                  |
|                          | SuperSOT™-3                                     |                  |
|                          | SuperSOT™-6                                     |                  |
|                          | SuperSOT™-8                                     |                  |
|                          | SupreMOS®                                       |                  |
|                          | SyncFET™  |                  |

\*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

**DISCLAIMER**

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

**LIFE SUPPORT POLICY**

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

**ANTI-COUNTERFEITING POLICY**

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support. Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

**PRODUCT STATUS DEFINITIONS**

**Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

# Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Fairchild Semiconductor:](#)

[FDP8030L](#)